

Title (en)

Passivation layer on a semiconductor device with a ferroelectric layer

Title (de)

Passivierungsschicht auf einer Halbleitervorrichtung mit einer ferroelektrischen Schicht

Title (fr)

Couche de passivation sur un dispositif semi-conducteur avec une couche ferroélectrique

Publication

**EP 1256979 B1 20060628 (EN)**

Application

**EP 01123445 A 20010928**

Priority

JP 2001141991 A 20010511

Abstract (en)

[origin: EP1256979A1] A semiconductor device includes at least a ferroelectric or high-dielectric-constant film and a surface coating that have been stacked in this order over a substrate. The surface coating is made of an acrylic resin. <IMAGE>

IPC 8 full level

**H01L 23/29** (2006.01); **H01L 23/556** (2006.01); **H10B 12/00** (2023.01); **H10B 20/00** (2023.01); **H10B 69/00** (2023.01); **H01L 21/02** (2006.01)

CPC (source: EP KR US)

**H01L 23/293** (2013.01 - EP US); **H01L 23/556** (2013.01 - EP US); **H10B 53/00** (2023.02 - EP US); **H10B 99/00** (2023.02 - KR); **H01L 28/55** (2013.01 - EP US); **H01L 2924/0002** (2013.01 - EP US); **H10B 53/30** (2023.02 - EP US)

C-Set (source: EP US)

**H01L 2924/0002** + **H01L 2924/00**

Cited by

WO2004077532A1

Designated contracting state (EPC)

DE FR GB NL

DOCDB simple family (publication)

**EP 1256979 A1 20021113**; **EP 1256979 B1 20060628**; DE 60121137 D1 20060810; DE 60121137 T2 20061116; JP 2002343941 A 20021129; JP 3977997 B2 20070919; KR 100840821 B1 20080623; KR 20020086823 A 20021120; TW 504821 B 20021001; US 2002167032 A1 20021114; US 6730948 B2 20040504

DOCDB simple family (application)

**EP 01123445 A 20010928**; DE 60121137 T 20010928; JP 2001141991 A 20010511; KR 20010074071 A 20011127; TW 90123920 A 20010927; US 96894101 A 20011003